



Response Under 37 C.F.R. § 1.116 #15

Expedited Procedure
Group Art Unit 2826

Amalt
12/9/02
aps

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION OF

Confirmation No.: 1868

HAMADA

Group Art Unit: 2826

Appln. No.: 09/663,340

Examiner: Mond, Johannes

Filed: September 15, 2000

Title: POWER SEMICONDUCTOR DEVICE AND PRODUCTION METHOD FOR THE
SAME

December 4, 2002

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AMENDMENT UNDER 37 C.F.R. § 1.116

Hon. Commissioner of Patents

Box AF

Washington, D.C. 20231

Sir:

In response to the final Office Action dated September 4, 2002, please enter the
following amendments and remarks:

RECEIVED
DEC - 6 2002
IC 2800 MAIL ROOM

IN THE CLAIMS:

Please amend claims 1 and 13 as follows:

- C1
- Sub D17
1. (Twice Amended) A semiconductor device comprising:
a body region of a first conductivity type formed in a semiconductor substrate and
having a major surface opposite to a surface shared between the semiconductor substrate and
the body region;
a plurality of trench gates extending through the body region;
a plurality of first semiconductor regions of a second conductivity type that is different
from the first conductivity type, the first semiconductor regions having a first depth as
measured from said major surface of the body region, at least a portion of the first
semiconductor regions flanking the trench gates on both of their sides and being in contact
with said trench gates via films bordering and insulating the trench gates; and